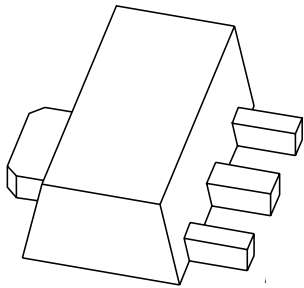


# DATA SHEET



## **PXT4403** PNP switching transistor

Product data sheet  
Supersedes data of 1999 Apr 14

2004 Nov 22

# PNP switching transistor

# PXT4403

### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

### APPLICATIONS

- Switching and linear amplification.

### DESCRIPTION

PNP switching transistor in a SOT89 plastic package.  
NPN complement: PXT4401.

### MARKING

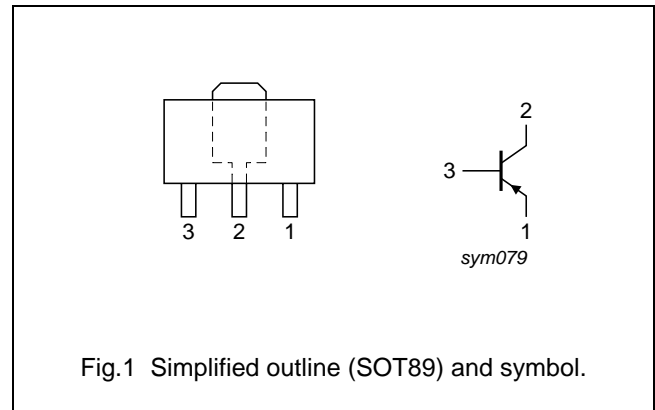
| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| PXT4403     | *2T                         |

### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

### PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | emitter     |
| 2   | collector   |
| 3   | base        |



### ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |  |         |
|-------------|---------|--|---------|
|             | NAME    | DESCRIPTION  | VERSION |
| PXT4403     | SC-62   | plastic surface mounted package; collector pad for good heat transfer; 3 leads | SOT89   |

PNP switching transistor

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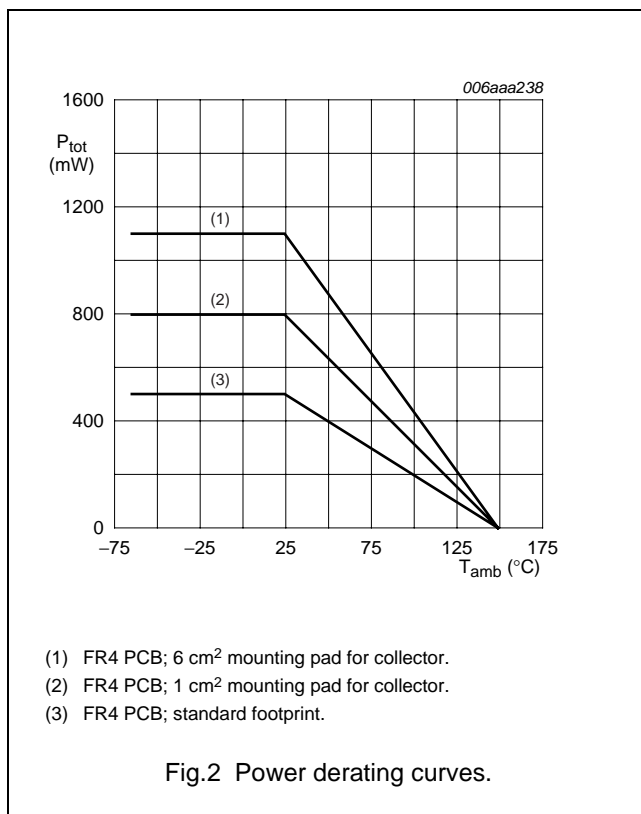
**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                 | CONDITIONS   | MIN. | MAX.              | UNIT        |
|------------------|---------------------------|--|------|-------------------|-------------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter   | –    | –40               | V           |
| V <sub>CEO</sub> | collector-emitter voltage | open base  | –    | –40               | V           |
| V <sub>EBO</sub> | emitter-base voltage      | open collector   | –    | –5                | V           |
| I <sub>C</sub>   | collector current (DC)    |  | –    | –600              | mA          |
| I <sub>CM</sub>  | peak collector current    |  | –    | –800              | mA          |
| I <sub>BM</sub>  | peak base current         |  | –    | –200              | mA          |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C<br>note 1<br>note 2<br>note 3 | –    | 0.5<br>0.8<br>1.1 | W<br>W<br>W |
| T <sub>stg</sub> | storage temperature       |  | –65  | +150              | °C          |
| T <sub>j</sub>   | junction temperature      |  | –    | 150               | °C          |
| T <sub>amb</sub> | ambient temperature       |  | –65  | +150              | °C          |

**Notes**

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



PNP switching transistor

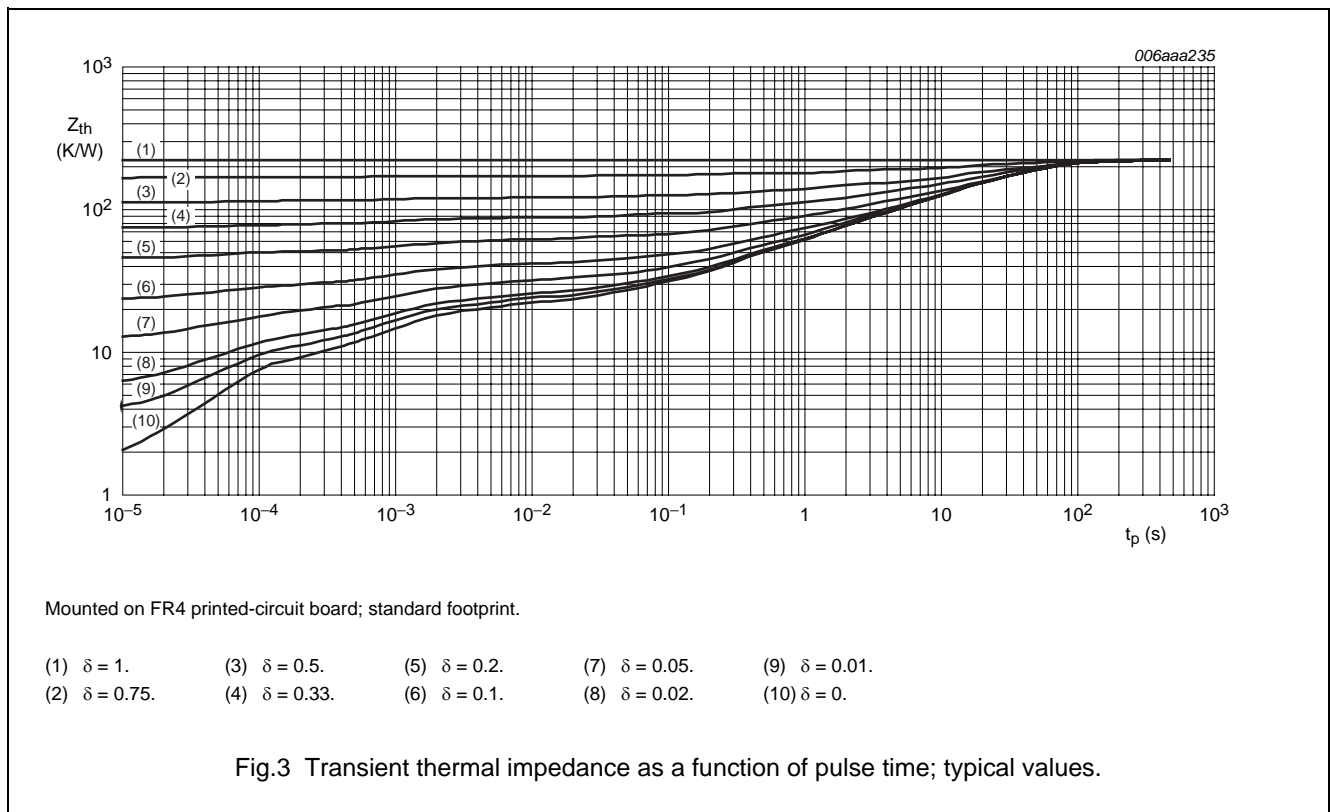
PXT4403

**THERMAL CHARACTERISTICS**

| SYMBOL               | PARAMETER   | CONDITIONS  | VALUE | UNIT |
|----------------------|---|-------------|-------|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient         | in free air |       |      |
|                      |   | note 1      | 250   | K/W  |
|                      |   | note 2      | 156   | K/W  |
|                      |   | note 3      | 113   | K/W  |
| R <sub>th(j-s)</sub> | thermal resistance from junction to soldering point |             | 30    | K/W  |

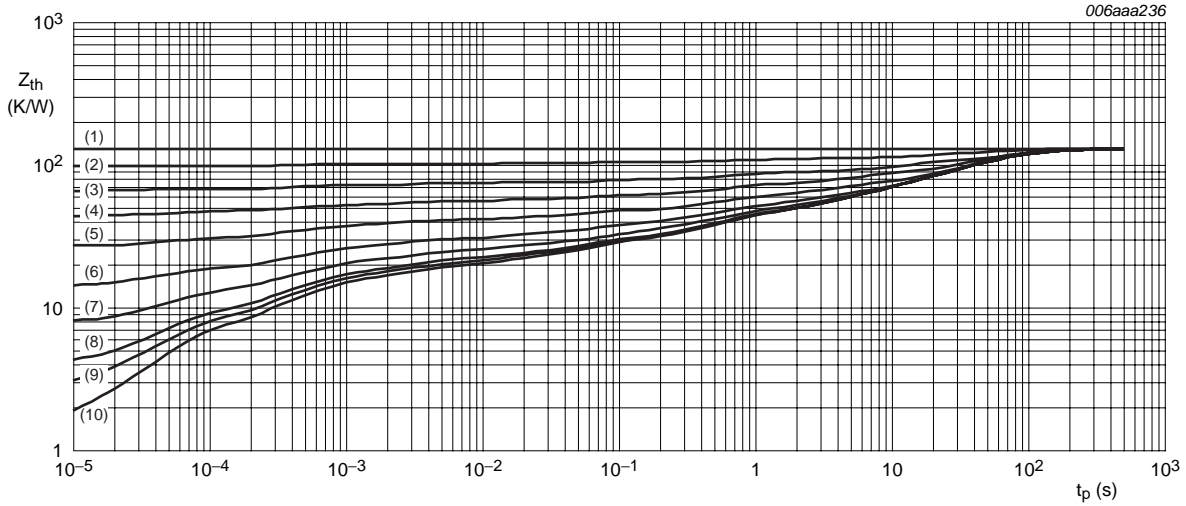
**Notes**

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



# PNP switching transistor

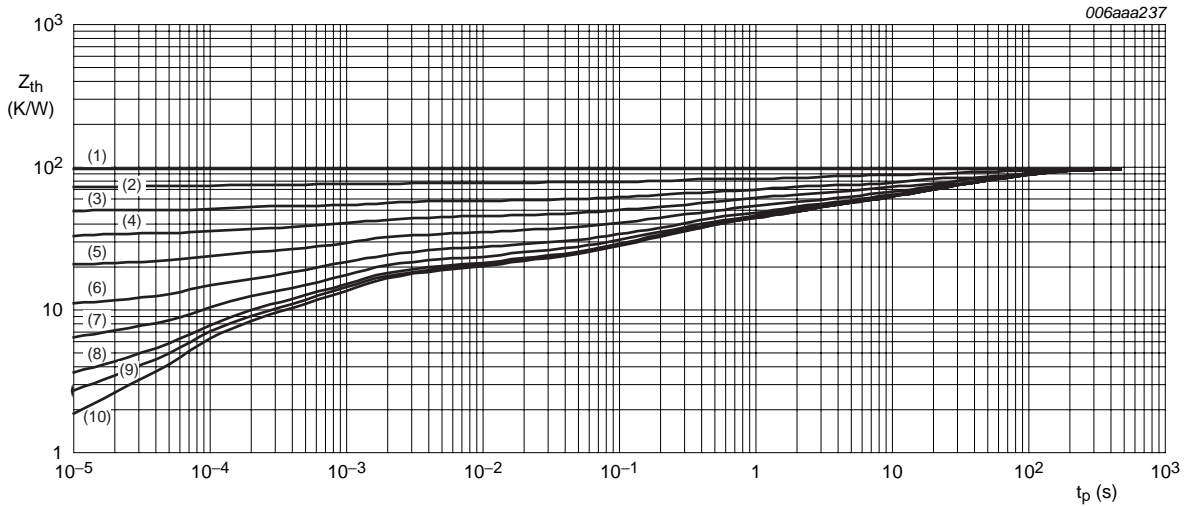
# PXT4403



Mounted on FR4 printed-circuit board; mounting pad for collector 1 cm<sup>2</sup>.

- (1)  $\delta = 1.$       (3)  $\delta = 0.5.$       (5)  $\delta = 0.2.$       (7)  $\delta = 0.05.$       (9)  $\delta = 0.01.$
- (2)  $\delta = 0.75.$       (4)  $\delta = 0.33.$       (6)  $\delta = 0.1.$       (8)  $\delta = 0.02.$       (10)  $\delta = 0.$

Fig.4 Transient thermal impedance as a function of pulse time; typical values.



Mounted on FR4 printed-circuit board; mounting pad for collector 6 cm<sup>2</sup>.

- (1)  $\delta = 1.$       (3)  $\delta = 0.5.$       (5)  $\delta = 0.2.$       (7)  $\delta = 0.05.$       (9)  $\delta = 0.01.$
- (2)  $\delta = 0.75.$       (4)  $\delta = 0.33.$       (6)  $\delta = 0.1.$       (8)  $\delta = 0.02.$       (10)  $\delta = 0.$

Fig.5 Transient thermal impedance as a function of pulse time; typical values.

## PNP switching transistor

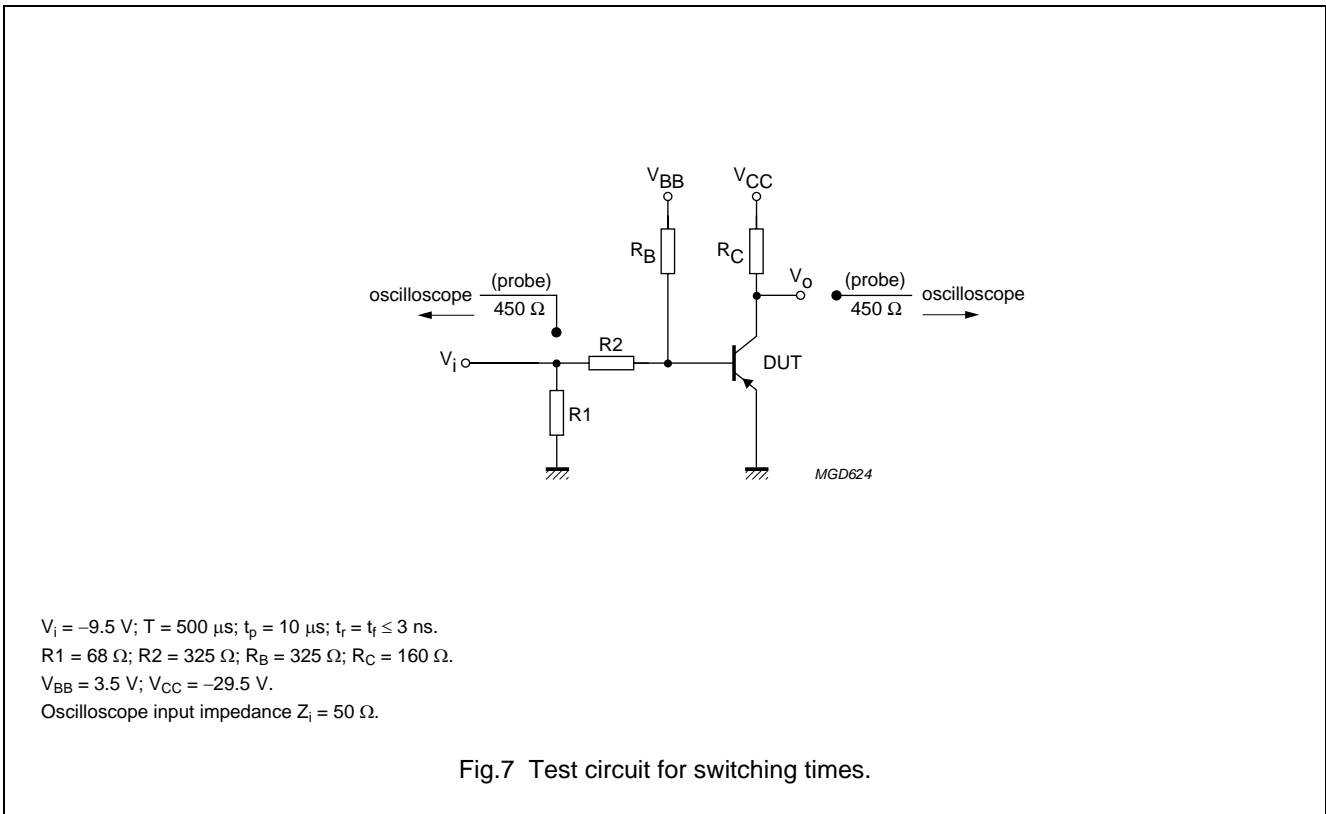
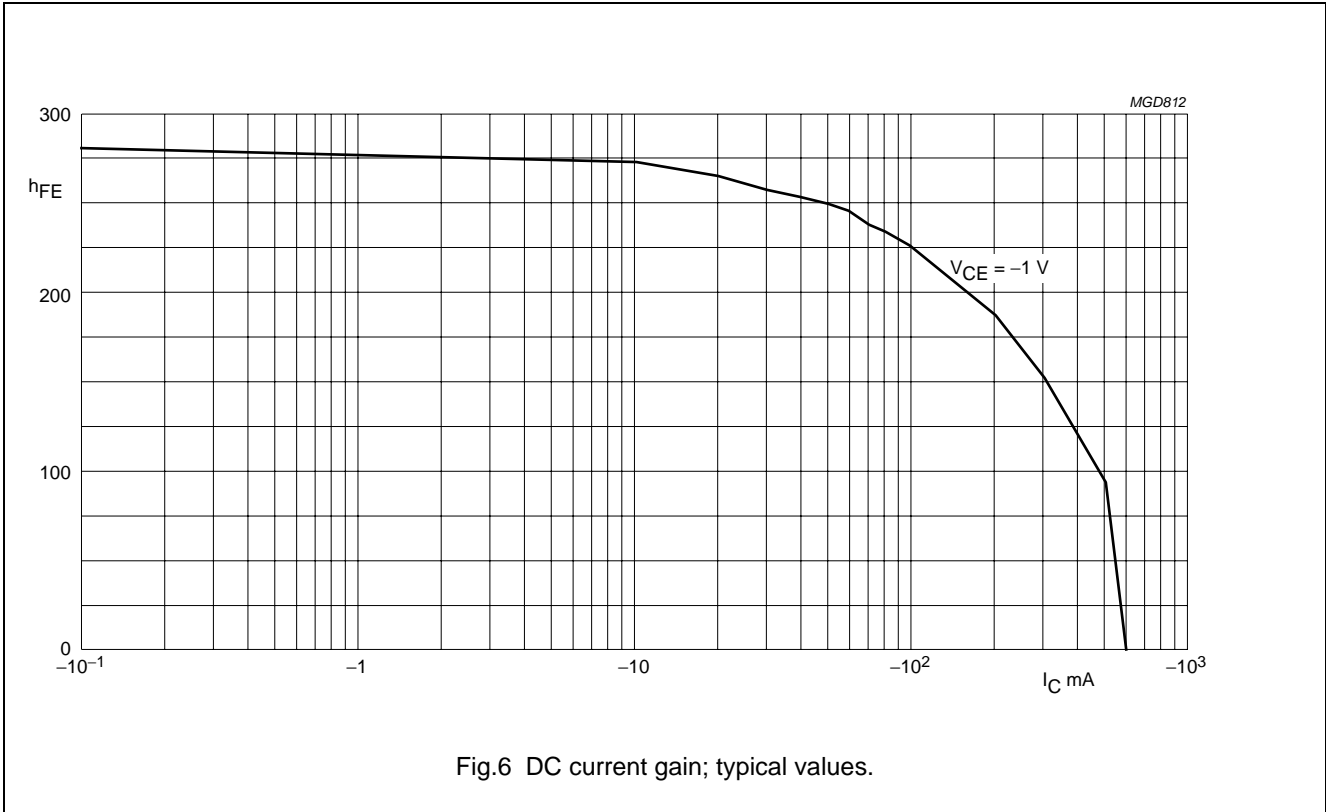
PXT4403

**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

| SYMBOL   | PARAMETER                            | CONDITIONS  | MIN. | MAX. | UNIT |
|--|--------------------------------------|---|------|------|------|
| $I_{CBO}$  | collector-base cut-off current       | $I_E = 0\text{ A}; V_{CB} = -40\text{ V}$   | –    | –50  | nA   |
| $I_{EBO}$  | emitter-base cut-off current         | $I_C = 0\text{ A}; V_{EB} = -5\text{ V}$  | –    | –50  | nA   |
| $h_{FE}$   | DC current gain                      | $I_C = -0.1\text{ mA}; V_{CE} = -1\text{ V}$                                      | 30   | –    |      |
|  |                                      | $I_C = -1\text{ mA}; V_{CE} = -1\text{ V}$  | 60   | –    |      |
|  |                                      | $I_C = -10\text{ mA}; V_{CE} = -1\text{ V}$                                       | 100  | –    |      |
|  |                                      | $I_C = -150\text{ mA}; V_{CE} = -2\text{ V}$                                      | 100  | 300  |      |
|  |                                      | $I_C = -500\text{ mA}; V_{CE} = -2\text{ V}$                                      | 20   | –    |      |
| $V_{CEsat}$  | collector-emitter saturation voltage | $I_C = -150\text{ mA}; I_B = -15\text{ mA}$                                       | –    | –400 | mV   |
|  |                                      | $I_C = -500\text{ mA}; I_B = -50\text{ mA}$                                       | –    | –750 | mV   |
| $V_{BEsat}$  | base-emitter saturation voltage      | $I_C = -150\text{ mA}; I_B = -15\text{ mA}$                                       | –    | –950 | mV   |
|  |                                      | $I_C = -500\text{ mA}; I_B = -50\text{ mA}$                                       | –    | –1.3 | V    |
| $C_c$  | collector capacitance                | $I_E = i_e = 0\text{ A}; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$                 | –    | 8.5  | pF   |
| $C_e$  | emitter capacitance                  | $I_C = i_c = 0\text{ A}; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$               | –    | 35   | pF   |
| $f_T$  | transition frequency                 | $I_C = -20\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$                  | 200  | –    | MHz  |
| <b>Switching times (between 10% and 90% levels); (see Fig.7)</b> |                                      |   |      |      |      |
| $t_{on}$   | turn-on time                         | $I_{Con} = -150\text{ mA}; I_{Bon} = -15\text{ mA};$<br>$I_{Boff} = 15\text{ mA}$ | –    | 40   | ns   |
| $t_d$  | delay time                           |   | –    | 15   | ns   |
| $t_r$  | rise time                            |   | –    | 30   | ns   |
| $t_{off}$  | turn-off time                        |   | –    | 350  | ns   |
| $t_s$  | storage time                         |   | –    | 300  | ns   |
| $t_f$  | fall time                            |   | –    | 50   | ns   |

PNP switching transistor

PXT4403



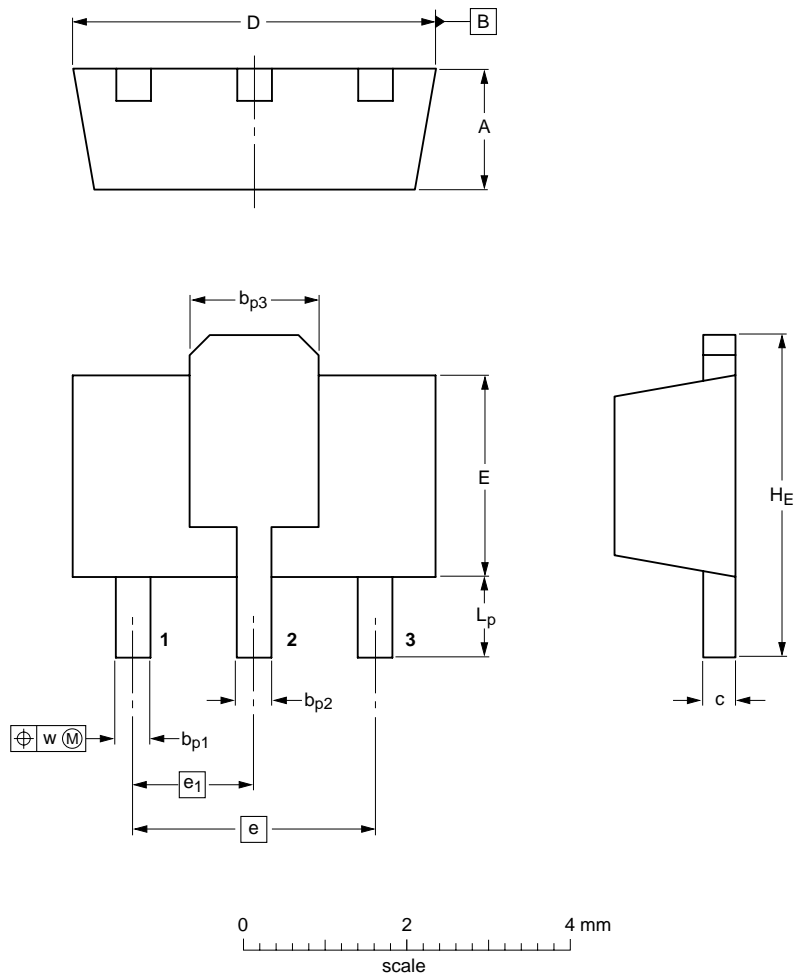
PNP switching transistor

PXT4403

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | b <sub>p1</sub> | b <sub>p2</sub> | b <sub>p3</sub> | c            | D          | E          | e   | e <sub>1</sub> | H <sub>E</sub> | L <sub>p</sub> | w    |
|------|------------|-----------------|-----------------|-----------------|--------------|------------|------------|-----|----------------|----------------|----------------|------|
| mm   | 1.6<br>1.4 | 0.48<br>0.35    | 0.53<br>0.40    | 1.8<br>1.4      | 0.44<br>0.23 | 4.6<br>4.4 | 2.6<br>2.4 | 3.0 | 1.5            | 4.25<br>3.75   | 1.2<br>0.8     | 0.13 |

| OUTLINE VERSION | REFERENCES |        |       |  | EUROPEAN PROJECTION | ISSUE DATE           |
|-----------------|------------|--------|-------|--|---------------------|----------------------|
|                 | IEC        | JEDEC  | JEITA |  |                     |                      |
| SOT89           |            | TO-243 | SC-62 |  |                     | 04-08-03<br>06-03-16 |



PNP switching transistor

PXT4403

**DATA SHEET STATUS**

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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